

FDMS86150

N-Channel Shielded Gate PowerTrench® MOSFET 100V, 80A, 4.85mΩ

Product Overview

For complete documentation, see the data sheet.

This N-Channel MOSFET is produced using an advanced PowerTrench® process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

Features

- Shielded Gate MOSFET Technology
- Max $r_{DS(on)}$ = 4.85 mΩ at $V_{GS} = 10$ V, $I_D = 16$ A
- Max $r_{DS(on)}$ = 7.8 mΩ at $V_{GS} = 6$ V, $I_D = 13$ A
- Advanced Package and Silicon combination for low $r_{DS(on)}$ and high efficiency
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

Applications

- DC-DC Merchant Power Supply

Part Electrical Specifications

Product	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	$V_{DS}^{(BR)}$ Min (V)	V_{GS}^{Max} (V)	$V_{GS}^{(th)}$ Max (V)	I_D^{Max} (A)	P_D^{Max} (W)	$R_{DS(on)}^{Max}$ @ $V_{GS} = 2.5$ V (mΩ)	$R_{DS(on)}^{Max}$ @ $V_{GS} = 4.5$ V (mΩ)	$R_{DS(on)}^{Max}$ @ $V_{GS} = 10$ V (mΩ)	Q_g^{Typ} @ $V_{GS} = 4.5$ V (nC)	Q_g^{Typ} @ $V_{GS} = 10$ V (nC)	C_{iss}^{Typ} (pF)	Package Type
FDMS86150	1.6187		Active	N-Channel	Single	100	±20	4	80	156	-	-	4.85	-	25	3055	PQFN-8